In the Drawings:

Enclosed are corrected drawing sheets for Figs. 1, 4B, 5B, 13A, 14A-14C, 15A-15C, 16A. Subject to the approval of the Examiner, it is respectfully requested that the new drawing sheets be substituted for the originally filed drawing sheets for Figs. 1, 4B, 5B, 13A, 14A-14C, 15A-15C, 16A. A copy of the original drawing sheets with changes indicated in red, is also attached.

In the Specification:

Please replace the paragraphs in the specification as indicated below. Marked up copies of the amended paragraphs illustrating the changes are shown in the Appendix to this Response.

Please replace the two paragraphs from page 10, line 10 through page 11, line 2, with the two paragraphs shown below.

As shown in Figure 9B, a source/drain/gate impurity implant is then performed to form the source and drain regions of the device of the present invention. The implant is such that the nitride 150 covering the channel area prevents implantation of the impurity into the channel region. Depending on the device size and strength of the impurity implant, the nitride 110 may be supplanted by an additional layer of oxide formed between nitride 110 and second nitride 155.

A1

For an N-channel device, arsenic or phosphorous may be deposited to a concentration of approximately 2-4x10^{15}/cm^3 at energies of approximately 15-20 KeV (arsenic) or 7-10 KeV (phosphorous). For a P-channel device, boron may be implanted into a concentration of 2-3x10^{15}/cm^3 at energies of approximately 1.5-2.5 KeV. Zero degree tilt implants are used for these embodiments. The implants are then subsequently annealed in a rapid thermal anneal for approximately 5-10 minutes at a temperature of 1000-1025°C.

Please replace the paragraph at page 12, lines 13-22, with the paragraph below.

Next, as shown in Figures 15A-15C, a directional etch of the TEOS 210 and the first nitride layer opens two vias 240,245 in the substrate, as well as removing the first nitride over the polysilicon 122, exposing the underlying silicon 122. Following via formation, a gate oxide 242 may be grown by immersing the structure in an oxygen-containing atmosphere for two minutes. Following gate oxide growth, a

A2